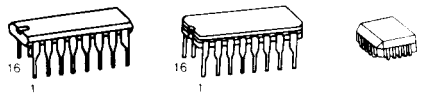
41951

HS-C²MOS™ INTEGRATED CIRCUITS

PRELIMINARY DATA

3-TO-8 LINE DECODER

The M54/74HC138 is a high speed CMOS 3-TO-8 LINE DECODER fabricated in silicon gate C²MOS technology. It has the same high speed performance of LSTTL combined with true CMOS low power consumption. If the device is enabled, 3 binary select inputs (A, B and C) determine which one of the outputs will go low. If enable input G1 is held "L" level or either $\overline{G2A}$ or $\overline{G2B}$ is held "H" level, the decoding function is inhibited and all the 8 outputs go high. 3 enable inputs are provided to ease cascade connection and application of address decoder for memory systems.
All inputs are equipped with protection circuits against static discharge or transient excess voltage.



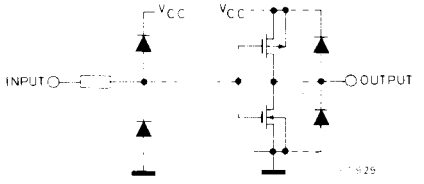
B1 Plastic Package | **F1** Ceramic Package | **C1** Chip Carrier

ORDERING NUMBERS: M54HC138 F1
M74HC138 B1
M74HC138 F1
M74HC138 C1

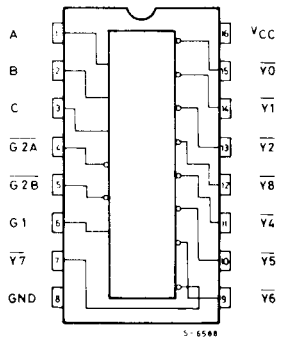
FEATURES

- High Speed
  t_{PD} = 17 ns (Typ.) at V_{CC} = 5V
- Low Power Dissipation
  I_{CC} = 4 μA (Max.) at T_A = 25°C
- High Noise Immunity
  $V_{NIH} = V_{NIL}$ = 28% V_{CC} (Min.)
- Output Drive Capability
  10 LSTTL Loads
- Symmetrical Output Impedance
  $|I_{OH}| = I_{OL}$ = 4 mA (Min.)
- Balanced Propagation Delays
  $t_{PLH} = t_{PHL}$
- Wide Operating Voltage Range
  V_{CC} (opr) = 2V to 6V
- Pin and Function compatible with 54/74LS138

INPUT AND OUTPUT EQUIVALENT CIRCUIT

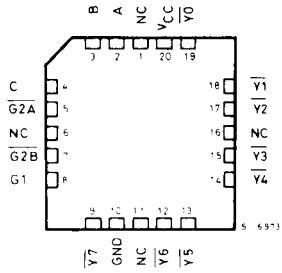


PIN CONNECTIONS
(top view)



Dual in line

CHIP CARRIER

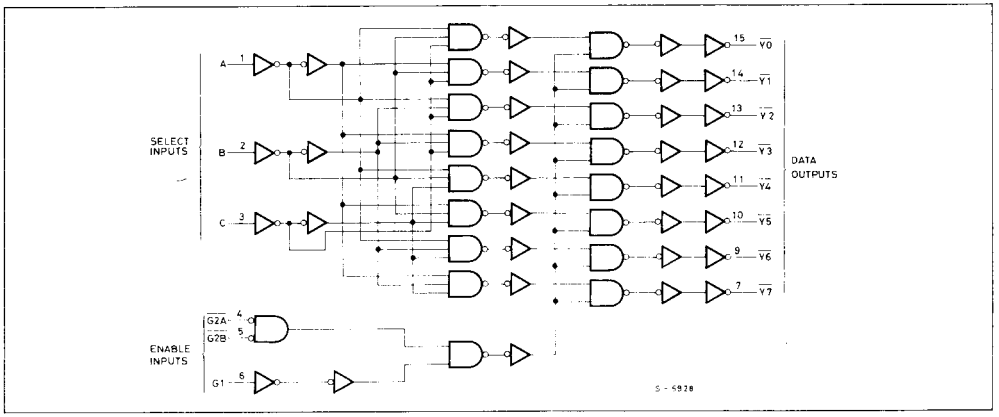


NC = No Internal Connection

TRUTH TABLE

INPUTS						OUTPUTS								SELECTED OUTPUT
ENABLE			SELECT											
G1	$\overline{G2A}$	$\overline{G2B}$	C	B	A	$\overline{Y0}$	$\overline{Y1}$	$\overline{Y2}$	$\overline{Y3}$	$\overline{Y4}$	$\overline{Y5}$	$\overline{Y6}$	$\overline{Y7}$	
L	*	*	*	*	*	H	H	H	H	H	H	H	H	NONE
*	H	*	*	*	*	H	H	H	H	H	H	H	H	NONE
*	*	H	*	*	*	H	H	H	H	H	H	H	H	NONE
H	L	L	L	L	L	L	H	H	H	H	H	H	H	$\overline{Y0}$
H	L	L	L	L	H	H	L	H	H	H	H	H	H	$\overline{Y1}$
H	L	L	L	H	L	H	H	L	H	H	H	H	H	$\overline{Y2}$
H	L	L	L	H	H	H	H	H	L	H	H	H	H	$\overline{Y3}$
H	L	L	H	L	L	H	H	H	H	L	H	H	H	$\overline{Y4}$
H	L	L	H	L	H	H	H	H	H	H	L	H	H	$\overline{Y5}$
H	L	L	H	H	L	H	H	H	H	H	H	L	H	$\overline{Y6}$
H	L	L	H	H	H	H	H	H	H	H	H	H	L	$\overline{Y7}$

LOGIC DIAGRAM



RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Limit		Unit
V_{CC}	Supply Voltage		2 to 6		V
V_I	Input Voltage		0 to V_{CC}		V
V_O	Output Voltage		0 to V_{CC}		V
T_A	Operating Temperature	74HC Series 54HC Series	40 to 85 55 to 125		°C
t_r, t_f	Input Rise and Fall Time	V_{CC}	2 V 4.5V 6 V	0 to 1000 0 to 500 0 to 400	ns

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	- 0.5 to 7	V
V_I	DC Input Voltage	0.5 to V_{CC} + 0.5	V
V_O	DC Output Voltage	0.5 to V_{CC} + 0.5	V
I_{IK}	DC Input Diode Current	± 20	mA
I_{OK}	DC Output Diode Current	± 20	mA
I_O	DC Output Source Sink Current Per Output Pin	± 25	mA
I_{CC} or I_{GND}	DC V_{CC} or Ground Current	± 50	mA
P_D	Power Dissipation	500 (*)	mW
T_{stg}	Storage Temperature	- 65 to 150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

(*) 500 mW: ≅ 65°C derate to 300 mW by 10 mW/°C: 65°C to 85°C.

DC SPECIFICATIONS

Symbol	Parameter	V_{CC}	Test Condition		T_A = 25°C 54HC and 74HC			-40 to 85°C 74HC		-55 to 125°C 54HC		Unit
					Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
V_{IH}	High Level Input Voltage	2.0			1.5	—	—	1.5	—	1.5	—	V
		4.5			3.15	—	—	3.15	—	3.15	—	
		6.0			4.2	—	—	4.2	—	4.2	—	
V_{IL}	Low Level Input Voltage	2.0			—	—	0.5	—	0.5	—	0.5	V
		4.5			—	—	1.35	—	1.35	—	1.35	
		6.0			—	—	1.8	—	1.8	—	1.8	
V_{OH}	High Level Output Voltage	2.0	V_I	I_O	1.9	2.0	—	1.9	—	1.9	—	V
		4.5	V_{IH} or V_{IL}	-20 μA	4.4	4.5	—	4.4	—	4.4	—	
		6.0			5.9	6.0	—	5.9	—	5.9	—	
		4.5		-4.0 mA	4.18	4.31	—	4.13	—	4.10	—	
		6.0		-5.2 mA	5.68	5.8	—	5.63	—	5.60	—	
V_{OL}	Low Level Output Voltage	2.0			—	0	0.1	—	0.1	—	0.1	V
		4.5	V_{IH} or V_{IL}	20 μA	—	0	0.1	—	0.1	—	0.1	
		6.0			—	0	0.1	—	0.1	—	0.1	
		4.5		4.0 mA	—	0.17	0.26	—	0.33	—	0.40	
		6.0		5.2 mA	—	0.18	0.26	—	0.33	—	0.40	
I_I	Input Leakage Current	6.0	V_I = V_{CC} or GND		—	—	±0.1	—	±1		±1	μA
I_{CC}	Quiescent Supply Current	6.0	V_I = V_{CC} or GND		—	—	4	—	40		80	μA

AC ELECTRICAL CHARACTERISTICS (V_{CC} = 5V, T_A = 25°C, C_L = 15pF, Input $t_r = t_f$ = 6ns)

Symbol	Parameter	54HC and 74HC			Unit
		MIN.	TYP.	MAX.	
t_{TLH} t_{THL}	Output Transition Time		4	8	ns
t_{PLH} t_{PHL}	Propagation Delay Time (A, B, C - $\overline{Y}$)		20	32	ns
t_{PLH} t_{PHL}	Propagation Delay Time (G, $\overline{G}$ - $\overline{Y}$)		17	27	ns

AC ELECTRICAL CHARACTERISTICS (C_L = 50pF, Input $t_r = t_f$ = 6ns)

Symbol	Parameter	V_{CC}	Test Condition	T_A = 25°C 54HC and 74HC			−40 to 85°C 74HC		55 to 125°C 54HC		Unit
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
t_{TLH} t_{THL}	Output Transition Time	2.0		—	30	75	—	90			ns
		4.5		—	8	15	—	18			
		6.0		—	7	13	—	16			
t_{PLH} t_{PHL}	Propagation Delay Time (A, B,C - $\overline{Y}$)	2.0		—	72	175	—	210			ns
		4.5		—	23	35	—	42			
		6.0		—	20	30	—	36			
t_{PLH} t_{PHL}	Propagation Delay Time (G, $\overline{G}$-$\overline{Y}$)	2.0		—	62	160	—	195			ns
		4.5		—	20	32	—	39			
		6.0		—	17	28	—	34			
C_{IN}	Input Capacitance			—	5	10	—	10			pF
C_{PD} (*)	Power Dissipation Capacitance			—	57	—	—	—			

Note (*) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the following equation.

$I_{CC(opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$